

Integrated Power Hybrid IC for Appliance Motor Drive Applications

IRAM136-1561A **MOTION ** Series 15A, 600V with Open Emitter Pins

Description

International Rectifier's IRAM136-1561A is a 15A, 600V Integrated Power Hybrid IC with Open Emitter pins for advanced Appliance Motor Drives applications such as energy efficient Washing Machine and Refrigerator Compressor Drivers. IR's technology offers an extremely compact, high performance AC motor-driver in a single isolated package to simplify design.

This advanced HIC is a combination of IR's low $V_{CE\ (on)}$ Trench IGBT technology and the industry benchmark 3 phase high voltage, high speed driver (3.3V compatible) in a fully isolated thermally enhanced package. A built-in high precision temperature monitor and over-current protection feature, along with the short-circuit rated IGBTs and integrated under-voltage lockout function, deliver high level of protection and fail-safe operation. Using a Single in line package with full transfer mold structure and CTI>600 minimizes PCB space and resolves isolation problems to heatsink.

Features

- Integrated gate drivers and bootstrap diodes
- Temperature monitor
- Protection shutdown pin
- Low V_{CE (on)} Trench IGBT technology
- Undervoltage lockout for all channels
- Matched propagation delay for all channels
- 3.3V Schmitt-triggered input logic
- Cross-conduction prevention logic
- Motor Power up to 1.5kW / 85~253 Vac
- Isolation 2000VRMS min and CTI> 600
- RoHS Compliant
- Recognized by UL (File Number: E252584)



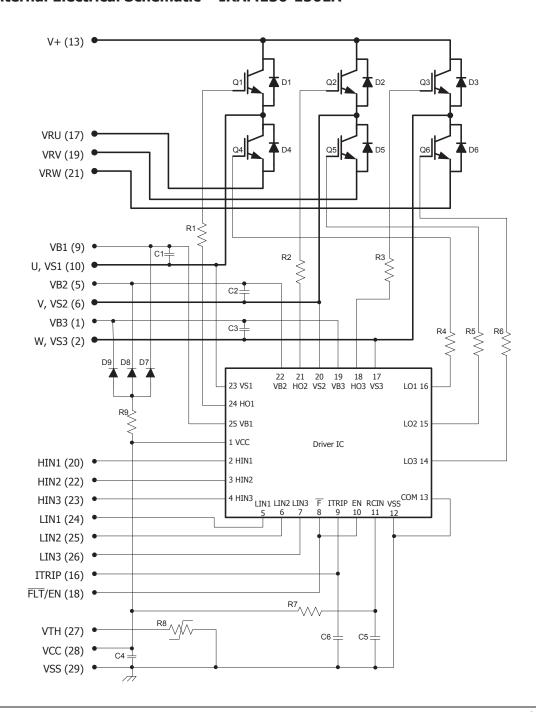
Absolute Maximum Ratings

| / LDS OT GICC I TG//III | | | |
|--|---|-------------|-----------|
| V _{CES} / V _{RRM} | IGBT/ FW Diode Blocking Voltage | 600 | V |
| V ⁺ | Positive Bus Input Voltage | 450 | ľ |
| I _o @ T _C =25°C | RMS Phase Current (Note 1) | 15 | |
| I _o @ T _C =100°C | RMS Phase Current (Note 1) | 7.5 | Α |
| I_{pk} | Maximum Peak Phase Current (Note 2) | 22.5 | |
| F_p | Maximum PWM Carrier Frequency | 20 | kHz |
| P_d | Maximum Power dissipation per IGBT @ T _C =25°C | 32 | W |
| V_{ISO} | Isolation Voltage (1min) | 2000 | V_{RMS} |
| T _J (IGBT & Diode & IC) | Maximum Operating Junction Temperature | +150 | |
| T _C | Operating Case Temperature Range | -20 to +100 | °C |
| T _{STG} | Storage Temperature Range | -40 to +125 | |
| Т | Mounting torque Range (M3 screw) | 0.8 to 1.0 | Nm |

Note 1: Sinusoidal Modulation at V⁺=320V, V_{CC}=15V, T₁=150°C, F_{PMM}=16kHz, MI=0.8, PF=0.6, See Figure 4.

Note 2: t_P <100ms, V_{CC} =15V, T_C =25°C, F_{PWM} =16kHz.

Internal Electrical Schematic - IRAM136-1561A





Absolute Maximum Ratings (Continued)

| Symbol | Parameter | Min | Max | Units | Conditions |
|----------------------|--|--------------------------|--|-------|---|
| I_{BDF} | Bootstrap Diode Peak Forward Current | | 1.0 | Α | $t_P = 10 \text{ms},$ $T_1 = 150 ^{\circ}\text{C}, T_C = 100 ^{\circ}\text{C}$ |
| P _{BR Peak} | Bootstrap Resistor Peak Power (Single Pulse) | | 15.0 | W | t_P =100 μ s, T_C =100°C ESR series |
| V _{S1,2,3} | High side floating supply offset voltage | V _{B1,2,3} - 20 | V _{B1,2,3} +0.3 | V | |
| V _{B1,2,3} | High side floating supply voltage | -0.3 | 600 | V | |
| V _{CC} | Low Side and logic fixed supply voltage | -0.3 | 20 | V | |
| V _{IN} | Input voltage LIN, HIN, I _{Trip} , FLT/EN | -0.3 | Lower of $(V_{SS}+15V)$ or $V_{CC}+0.3V$ | V | |

Inverter Section Electrical Characteristics

 V_{BIAS} (V_{CC} , $V_{BS1,2,3}$)=15V, T_1 =25°C, unless otherwise specified.

| Symbol | Parameter | Min | Тур | Max | Units | Conditions |
|---------------------------------|---|-----|------|------|-------|--|
| V _{(BR)CES} | Collector-to-Emitter Breakdown Voltage | 600 | | | V | V _{IN} =0V, I _C =250μA |
| $\Delta V_{(BR)CES} / \Delta T$ | Temperature Coeff. Of Breakdown Voltage | | 0.3 | | V/°C | V _{IN} =0V, I _C =1mA (25°C - 150°C) |
| V | Collector-to-Emitter Saturation | | 1.5 | 1.75 | V | I _C =7.5A, T _J =25°C |
| $V_{CE(ON)}$ | Voltage | | 1.7 | | ľ | I _C =7.5A, T _J =150°C |
| т | Zero Gate Voltage Collector | | 8 | 80 | | V _{IN} =0V, V ⁺ =600V |
| I_{CES} | Current | | 100 | | μA | V _{IN} =0V, V ⁺ =600V, T _J =150°C |
| V | Diada Farward Voltago Dran | | 1.8 | 2.4 | V | I _F =7.5A |
| V_{FM} | Diode Forward Voltage Drop | | 1.4 | | | I _F =7.5A, T _J =150°C |
| V | Bootstrap Diode Forward Voltage | | 1.65 | 1.8 | V | I _F =1A |
| V_{BDFM} | Drop | | 1.3 | | ľ | I _F =1A, T _J =150°C |
| R _{BR} | Bootstrap Resistor Value | | 22 | | Ω | T _J =25°C |
| $\Delta R_{BR}/R_{BR}$ | Bootstrap Resistor Tolerance | | | ±5 | % | T _J =25°C |
| C _{1,2,3,4} | V _{CC} / V _{BS} Capacitor Value | | 47 | | nF | T _J =25°C |
| C ₆ | Itrip Capacitor Value | | 1 | | nF | T ₃ =25°C |



Inverter Section Switching Characteristics

 V_{BIAS} (V_{CC} , $V_{BS1,2,3}$)=15V, T_{J} =25°C, unless otherwise specified.

| Symbol | Parameter | Min | Тур | Max | Units | Conditions | |
|------------------|-----------------------------------|-------------|-----|-----|--|---|--|
| E _{ON} | Turn-On Switching Loss | | 260 | 490 | | I _C =7.5A, V ⁺ =400V | |
| E _{OFF} | Turn-Off Switching Loss | | 135 | 230 | | V _{CC} =15V, L=1.2mH | |
| E _{TOT} | Total Switching Loss | | 395 | 720 | μJ | Energy losses include "tail" and | |
| E _{REC} | Diode Reverse Recovery energy | | 25 | 50 | | diode reverse recovery | |
| t_{RR} | Diode Reverse Recovery time | | 100 | | ns | See CT1 | |
| E _{ON} | Turn-on Switching Loss | | 380 | | | $I_C=7.5A, V^+=400V$ | |
| E _{OFF} | Turn-off Switching Loss | | 190 | | | V _{CC} =15V, L=1.2mH, T _J =150°C | |
| E _{TOT} | Total Switching Loss | | 570 | | μJ | Energy losses include "tail" and | |
| E _{REC} | Diode Reverse Recovery energy | | 75 | | | diode reverse recovery | |
| t _{RR} | Diode Reverse Recovery time | | 150 | | ns | See CT1 | |
| Q_{G} | Turn-On IGBT Gate Charge | | 25 | 38 | nC | $I_C=12A$, $V^+=400V$, $V_{GE}=15V$ | |
| RBSOA | Reverse Bias Safe Operating Area | FULL SQUARE | | | $T_J=150$ °C, $I_C=5A$, $V_P=600V$ $V^+=450V$, $V_{CC}=+15V$ to $0V$ See CT3 | | |
| SCSOA | Short Circuit Safe Operating Area | 5 | | | μs | $T_J=25^{\circ}\text{C}, V^+=400\text{V}, V_{GE}=+15\text{V to 0V}$ | |
| SCSOA | Short Circuit Safe Operating Area | 3 | | | μs | $T_J=100$ °C, V ⁺ = 400V, V _{GE} =+15V to 0V | |
| SCSOA | Short Circuit Safe Operating Area | 2 | | | μs | $T_J=150$ °C, V ⁺ = 360V, V _{GE} =+17.5V to 0V | |
| I_{CSC} | Short Circuit Collector Current | 16.5 | | | Α | $T_J=150$ °C, $V_{CE}=50V$, $V_{GE}=11V$ | |

Recommended Operating Conditions Driver Function

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltages are absolute referenced to COM. The V_S offset is tested with all supplies biased at 15V differential (Note 3)

| Symbol | Definition | Min | Тур | Max | Units |
|---------------------|--|----------------------|--------------------|----------------------|-------|
| V _{B1,2,3} | High side floating supply voltage | V _S +12.5 | V _S +15 | V _S +17.5 | V |
| V _{S1,2,3} | High side floating supply offset voltage | Note 4 | | 450 | V |
| V_{CC} | Low side and logic fixed supply voltage | 13.5 | 15 | 16.5 | V |
| V _{ITRIP} | I_{TRIP} input voltage | V_{SS} | | V _{SS} +5 | V |
| V_{IN} | Logic input voltage LIN, HIN, FLT/EN | V_{SS} | | V _{SS} +5 | V |
| HIN | High side PWM pulse width | 1 | | | μs |
| Deadtime | External dead time between HIN and LIN | 1 | | | μs |

Note 3: For more details, see IR21364 data sheet

Note 4: Logic operational for V_s from COM-5V to COM+600V. Logic state held for V_s from COM-5V to COM- V_{BS} . (please refer to DT97-3 for more details)



Static Electrical Characteristics Driver Function

 V_{BIAS} (V_{CC} , $V_{BS1,2,3}$)=15V, T_J =25°C, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM and are applicable to all six channels. (Note 3)

| Symbol | Definition | Min | Тур | Max | Units |
|---|--|------|------|------|-------|
| $V_{IN,th+}$ | Positive going input threshold for LIN, HIN, FLT/EN | 2.5 | | | V |
| V _{IN,th-} | Negative going input threshold for LIN, HIN, FLT/EN | | | 0.8 | V |
| V_{CCUV+}, V_{BSUV+} | V _{CC} /V _{BS} supply undervoltage, Positive going threshold | 10.6 | 11.1 | 11.6 | V |
| V _{CCUV-} , V _{BSUV-} | V _{CC} /V _{BS} supply undervoltage, Negative going threshold | 10.4 | 10.9 | 11.4 | V |
| V _{CCUVH} , V _{BSUVH} | V _{CC} and V _{BS} supply undervoltage lock-out hysteresis | | 0.2 | | V |
| I_{QBS} | Quiescent V _{BS} supply current | | | 150 | μA |
| I_{QCC} | Quiescent V _{CC} supply current | | | 3.2 | mA |
| I_{LK} | Offset Supply Leakage Current | | | 50 | μA |
| I_{IN+} | Input bias current V _{IN} =3.3V for LIN, HIN, FLT/EN | | 100 | 195 | μΑ |
| I_{IN-} | Input bias current V _{IN} =0V for LIN, HIN, FLT/EN | -1 | | | μA |
| I_{TRIP+} | I _{TRIP} bias current V _{T/ITRIP} =3.3V | | 3.3 | 6 | μA |
| I_{TRIP} | I _{TRIP} bias current V _{T/ITRIP} =0V | -1 | | | μΑ |
| V(I _{TRIP}) | I _{TRIP} threshold Voltage | 0.44 | 0.49 | 0.54 | V |
| V(I _{Trip,} HYS) | I _{TRIP} Input Hysteresis | | 0.07 | | V |
| R _{on_FLT} | Fault low on resistance | | 50 | 100 | Ω |

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC} , $V_{\text{BS1,2,3}}$)=15V, T_{J} =25°C, unless otherwise specified. Driver only timing unless otherwise specified.

| Symbol | Parameter | Min | Тур | Max | Units | Conditions |
|------------------------|---|------|-----|------|-------|--|
| T _{ON} | Input to Output propagation turn- on delay time (see fig.11) | | | 1.15 | μs | I _C =7.5A, V ⁺ =300V |
| T _{OFF} | Input to Output propagation turn- off delay time (see fig. 11) | | | 1.15 | μs | 1 _C -7.3A, V -300V |
| T _{FILIN} | Input filter time (HIN,LIN) | | 310 | | ns | $V_{IN}=0$ or $V_{IN}=5V$ |
| T _{FILEN} | Input filter time (FLT/EN) | 100 | 200 | | ns | $V_{IN}=0$ or $V_{IN}=5V$ |
| T _{EN} | EN low to six switch turn-off propagation delay (see fig. 3) | | | 1.35 | μs | V_{IN} =0 or V_{IN} =5V, V_{EN} =0 |
| T _{FLT} | I_{TRIP} to Fault propagation delay | 400 | 600 | 800 | ns | V_{IN} =0 or V_{IN} =5V, V_{ITRIP} =5V |
| T _{BLT-ITRIP} | I _{TRIP} Blanking Time | 100 | 150 | | ns | V_{IN} =0 or V_{IN} =5V, V_{ITRIP} =5V |
| T _{ITRIP} | I _{TRIP} to six switch turn-off propagation delay (see fig. 2) | | | 1.5 | μs | I _C =7.5A, V ⁺ =300V |
| D_T | Internal Dead Time injected by driver | 220 | 290 | 360 | ns | V_{IN} =0 or V_{IN} =5V |
| M _T | Matching Propagation Delay Time (On & Off) all channels | | 40 | 75 | ns | External dead time> 400ns |
| т | Post I_{TRIP} to six switch turn-off | 1.17 | 1.7 | 2.19 | ms | T _C = 25°C |
| T _{FLT-CLR} | clear time (see fig. 2) | 1 | 1.5 | 1.9 | 1115 | $T_C = 100$ °C |

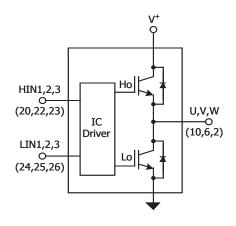
Thermal and Mechanical Characteristics

| Symbol | Parameter | Min | Тур | Max | Units | Conditions | |
|----------------------|-------------------------------|-----|-----|-----|-------|---|--|
| R _{th(J-C)} | Thermal resistance, per IGBT | | 3.2 | 3.8 | | Inverter Operating Condition | |
| R _{th(J-C)} | Thermal resistance, per Diode | | 5.0 | 6.0 | °C/W | Flat, greased surface. Heatsink compound thermal conductivity | |
| R _{th(C-S)} | Thermal resistance, C-S | | 0.1 | | | 1W/mK | |
| СТІ | Comparative Tracking Index | 600 | | | V | | |
| BKCurve | Curvature of module backside | 0 | 80 | | μm | Convex only | |

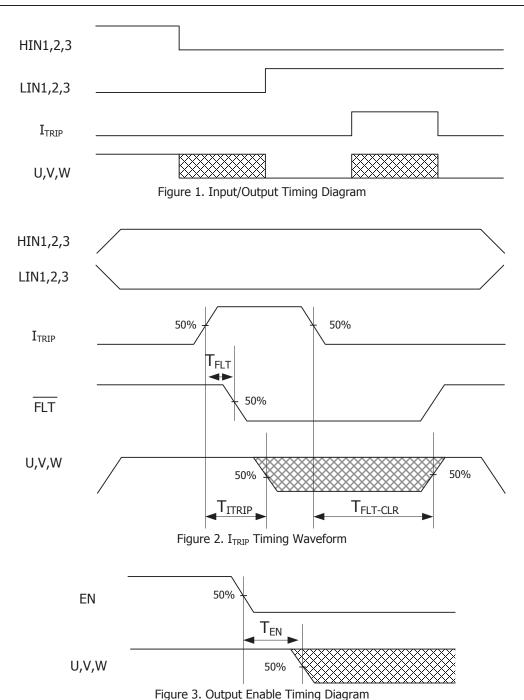
Internal NTC - Thermistor Characteristics

| Parameter | Definition | Min | Тур | Max | Units | Conditions |
|---------------------------|----------------------|-------|------|-------|-------|----------------------------------|
| R ₂₅ | Resistance | 44.65 | 47 | 49.35 | kΩ | T _C = 25°C |
| R ₁₂₅ | Resistance | 1.27 | 1.41 | 1.56 | kΩ | T _C = 125°C |
| В | B-constant (25-50°C) | 3989 | 4050 | 4111 | k | $R_2 = R_1 e^{[B(1/T2 - 1/T1)]}$ |
| Temperature Range | | -40 | | 125 | °C | |
| Typ. Dissipation constant | | | 1 | | mW/°C | T _C = 25°C |

Input-Output Logic Level Table



| FLT/EN | I_{TRIP} | HIN1,2,3 | LIN1,2,3 | U,V,W |
|--------|------------|----------|----------|-------|
| 1 | 0 | 1 | 0 | V+ |
| 1 | 0 | 0 | 1 | 0 |
| 1 | 0 | 0 | 0 | Off |
| 1 | 0 | 1 | 1 | Off |
| 1 | 1 | Χ | Χ | Off |
| 0 | Х | Х | Х | Off |



Note 5: The shaded area indicates that both high-side and low-side switches are off and therefore the half-bridge output voltage would be determined by the direction of current flow in the load.

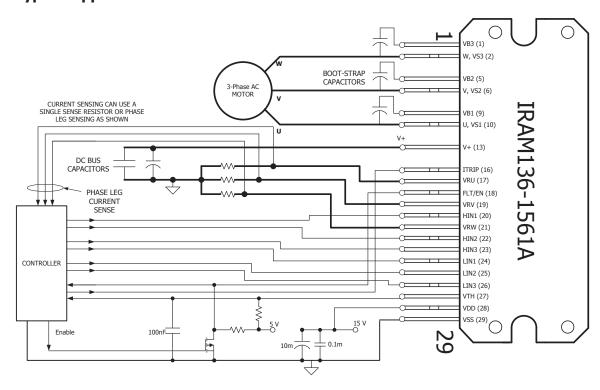
Module Pin-Out Description

| Pin | Name | Description |
|-----|----------------|---|
| 1 | VB3 | High Side Floating Supply Voltage 3 |
| 2 | W,VS3 | Output 3 - High Side Floating Supply Offset Voltage |
| 3 | na | none |
| 4 | na | none |
| 5 | VB2 | High Side Floating Supply voltage 2 |
| 6 | V,VS2 | Output 2 - High Side Floating Supply Offset Voltage |
| 7 | na | none |
| 8 | na | none |
| 9 | VB1 | High Side Floating Supply voltage 1 |
| 10 | U,VS1 | Output 1 - High Side Floating Supply Offset Voltage |
| 11 | na | none |
| 12 | na | none |
| 13 | V ⁺ | Positive Bus Input Voltage |
| 14 | na | none |
| 15 | na | none |
| 16 | I_{TRIP} | Current Protection Pin |
| 17 | VRU | Low Side Emitter Connection - Phase 1 |
| 18 | FLT/EN | Fault Output and Enable Pin |
| 19 | VRV | Low Side Emitter Connection - Phase 2 |
| 20 | HIN1 | Logic Input High Side Gate Driver - Phase 1 |
| 21 | VRW | Low Side Emitter Connection - Phase 3 |
| 22 | HIN2 | Logic Input High Side Gate Driver - Phase 2 |
| 23 | HIN3 | Logic Input High Side Gate Driver - Phase 3 |
| 24 | LIN1 | Logic Input Low Side Gate Driver - Phase 1 |
| 25 | LIN2 | Logic Input Low Side Gate Driver - Phase 2 |
| 26 | LIN3 | Logic Input Low Side Gate Driver - Phase 3 |
| 27 | V_{TH} | Temperature Feedback |
| 28 | V_{CC} | +15V Main Supply |
| 29 | V_{SS} | Negative Main Supply |





Typical Application Connection IRAM136-1561A



- 1. Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible to reduce ringing and EMI problems. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
- 2. In order to provide good decoupling between VCC-VSS and VB1,2,3-VS1,2,3 terminals, the capacitors shown connected between these terminals should be located very close to the module pins. Additional high frequency capacitors, typically $0.1\mu\text{F}$, are strongly recommended.
- 3. Value of the boot-strap capacitors depends upon the switching frequency. Their selection should be made based on IR design tip DN 98-2a, application note AN-1044 or Figure 11. Bootstrap capacitor value must be selected to limit the power dissipation of the internal resistor in series with the VCC. (see maximum ratings Table on page 3).
- 4. After approx. 2ms the FAULT is reset. (see Dynamic Characteristics Table on page 5).
- 5. PWM generator must be disabled within Fault duration to guarantee shutdown of the system, overcurrent condition must be cleared before resuming operation.

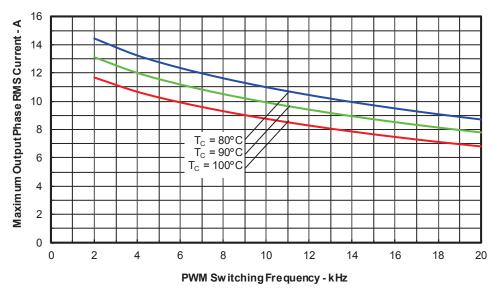


Figure 4. Maximum Sinusoidal Phase Current vs. PWM Switching Frequency Sinusoidal Modulation, V^+ =400V, T_3 =150°C, MI=0.8, PF=0.6, fmod=50Hz

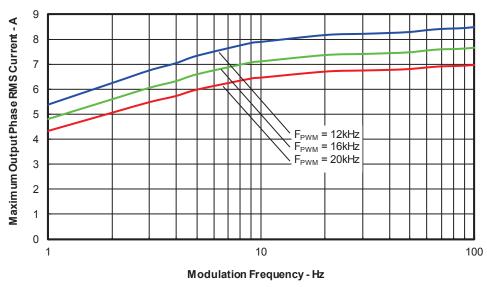


Figure 5. Maximum Sinusoidal Phase Current vs. Modulation Frequency Sinusoidal Modulation, V^+ =400V, T_3 =150°C, T_C =100°C, MI=0.8, PF=0.6

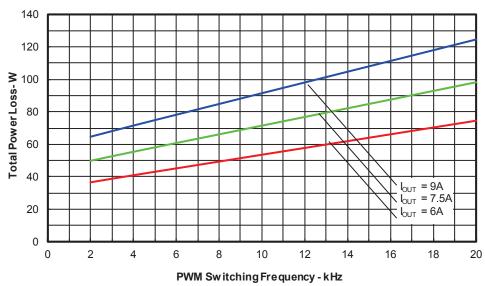


Figure 6. Total Power Losses vs. PWM Switching Frequency Sinusoidal Modulation, V^+ =400V, T_J =150°C, MI=0.8, PF=0.6, fmod=50Hz

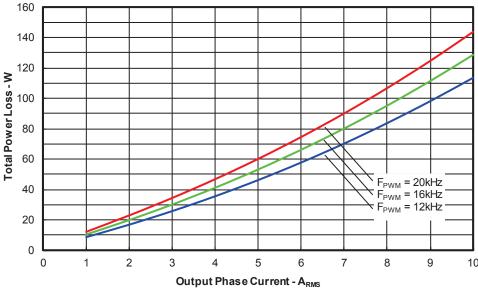


Figure 7. Total Power Losses vs. Output Phase Current Sinusoidal Modulation, V^+ =400V, T_3 =150°C, MI=0.8, PF=0.6, fmod=50Hz

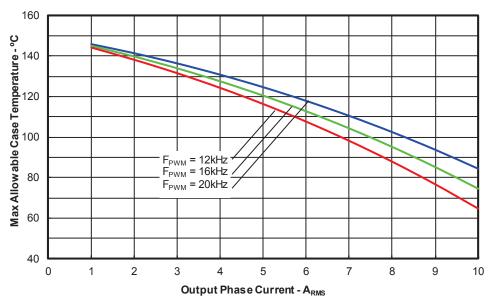


Figure 8. Maximum Allowable Case Temperature vs. Output RMS Current per Phase Sinusoidal Modulation, V^+ =400V, T_J =150°C, MI=0.8, PF=0.6, fmod=50Hz

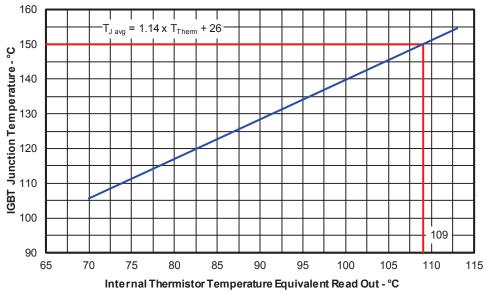


Figure 9. Estimated Maximum IGBT Junction Temperature vs. Thermistor Temperature Sinusoidal Modulation, V+=400V, Iphase=6Arms, fsw=16kHz, fmod=50Hz, MI=0.8, PF=0.6

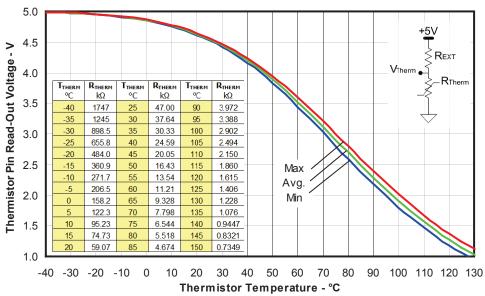


Figure 10. Thermistor Readout vs. Temperature (7.5kohm R_{EXT} pull-down resistor) and Normal Thermistor Resistance values vs. Temperature Table.

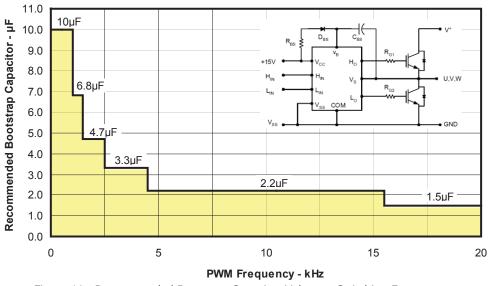
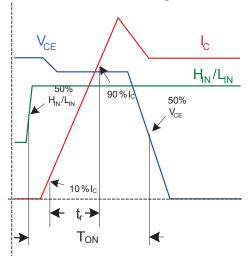


Figure 11. Recommended Bootstrap Capacitor Value vs. Switching Frequency

Figure 12. Switching Parameter Definitions



V_{CE}

90 % b

10 % l

10 % l

T_{OFF}

10 % l

Figure 12a. Input to Output propagation turn-on delay time.

Figure 12b. Input to Output propagation turn-off delay time.

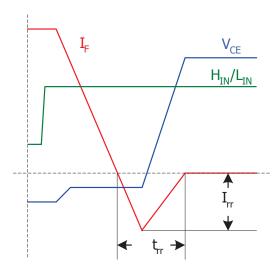
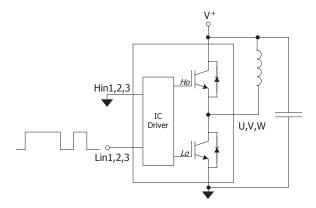


Figure 12c. Diode Reverse Recovery.



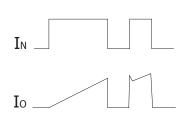
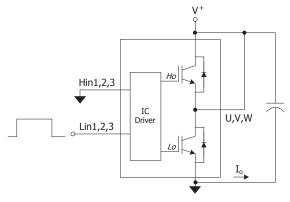


Figure CT1. Switching Loss Circuit



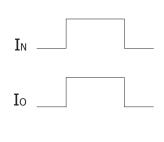
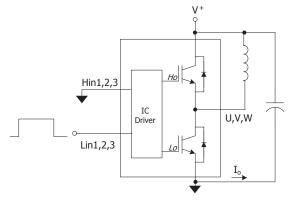


Figure CT2. S.C.SOA Circuit



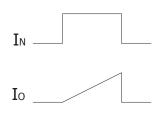
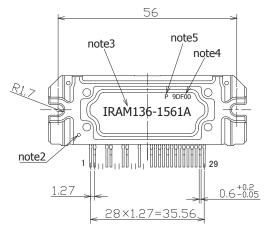
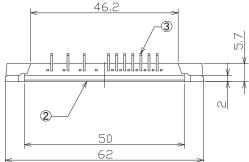


Figure CT3. R.B.SOA Circuit

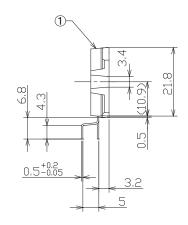


Package Outline IRAM136-1561A





missing pin: 3,4,7,8,11,12,14,15



note1: Unit Tolerance is ± 0.5 mm, Unless Otherwise Specified.

note2: Mirror Surface Mark indicates Pin1 Identification.

note3: Part Number Marking.

Characters Font in this drawing differs from

Font shown on Module.

note4: Lot Code Marking.

Characters Font in this drawing differs from

Font shown on Module.

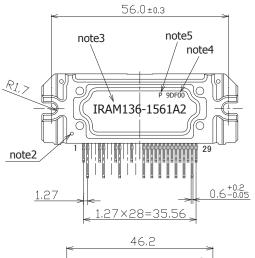
note5: "P" Character denotes Lead Free.

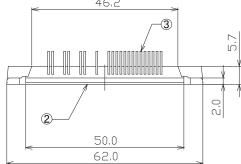
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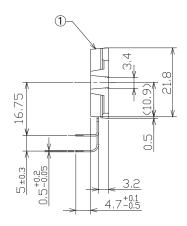
Dimensions in mm For mounting instruction see AN-1049

Package Outline IRAM136-1561A2





missing pin: 3,4,7,8,11,12,14,15



note1: Unit Tolerance is +0.5mm, Unless Otherwise Specified.

note2: Mirror Surface Mark indicates Pin1 Identification.

note3: Part Number Marking.

Characters Font in this drawing differs from

Font shown on Module.

note4: Lot Code Marking.

Characters Font in this drawing differs from

Font shown on Module.

note5: "P" Character denotes Lead Free.

Characters Font in this drawing differs from

Font shown on Module.

Dimensions in mm For mounting instruction see AN-1049



Data and Specifications are subject to change without notice

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